



SANYO Semiconductors

DATA SHEET

2SK3707 — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- 4V drive.
- Motor driver, DC / DC converter.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		100	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		20	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	80	A
Allowable Power Dissipation	P _D		2.0	W
		Tc=25°C	25	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	E _{AS}		125	mJ
Avalanche Current *2	I _{AV}		20	A

Note : *1 V_{DD}=20V, L=500μH, I_{AV}=20A

*2 L≤500μH, single pulse

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR) _{DSS}	I _D =1mA, V _{GS} =0	100			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±16V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	1.2		2.6	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =10A	11	17		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =10A, V _{GS} =10V		45	60	mΩ
	R _{DS(on)2}	I _D =10A, V _{GS} =4V		56	80	mΩ

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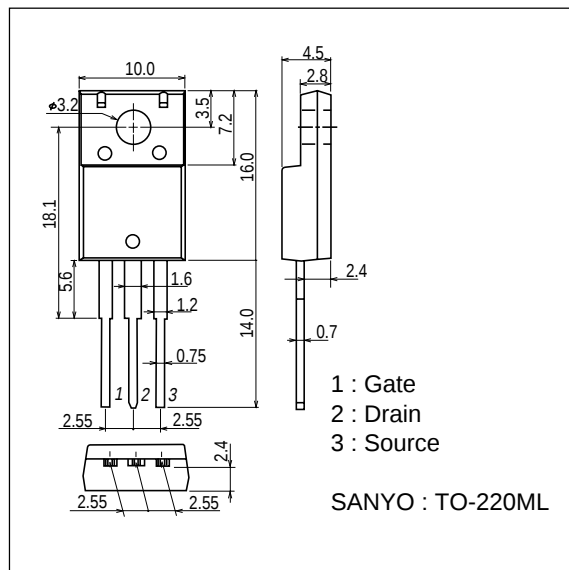
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	$V_{DS}=20V, f=1MHz$		2150		pF
Output Capacitance	Coss	$V_{DS}=20V, f=1MHz$		160		pF
Reverse Transfer Capacitance	Crss	$V_{DS}=20V, f=1MHz$		110		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		19.5		ns
Rise Time	t_r	See specified Test Circuit.		30		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		185		ns
Fall Time	t_f	See specified Test Circuit.		60		ns
Total Gate Charge	Qg	$V_{DS}=50V, V_{GS}=10V, I_D=20A$		44		nC
Gate-to-Source Charge	Qgs	$V_{DS}=50V, V_{GS}=10V, I_D=20A$		7.8		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=50V, V_{GS}=10V, I_D=20A$		9.8		nC
Diode Forward Voltage	V_{SD}	$I_S=20A, V_{GS}=0$		0.95	1.2	V

Marking : K3707

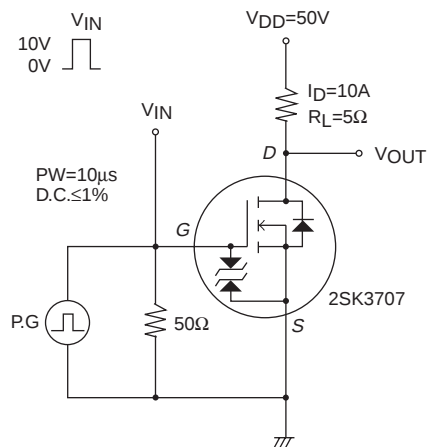
Package Dimensions

unit : mm

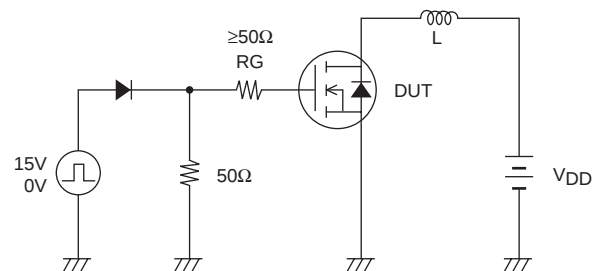
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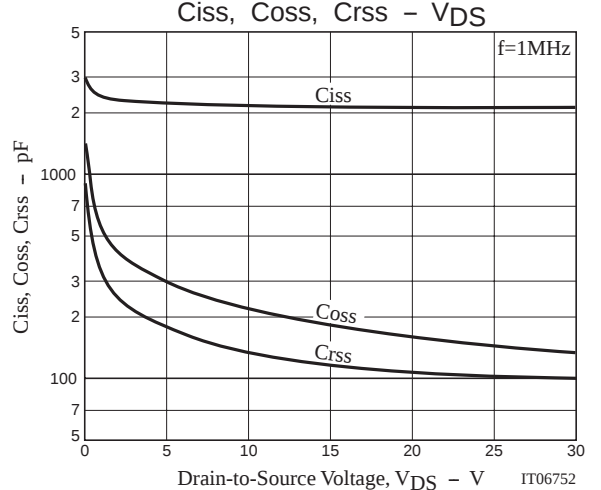
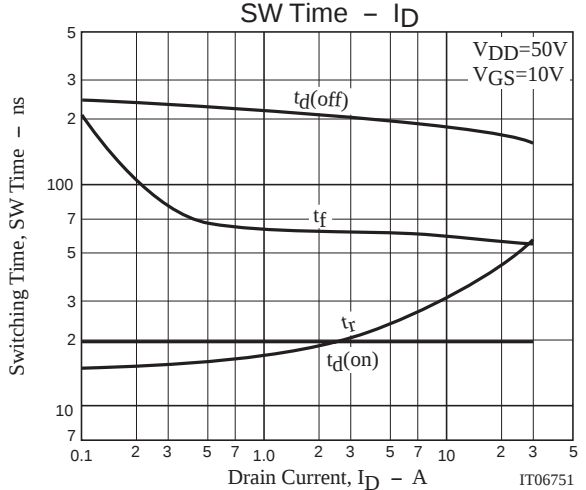
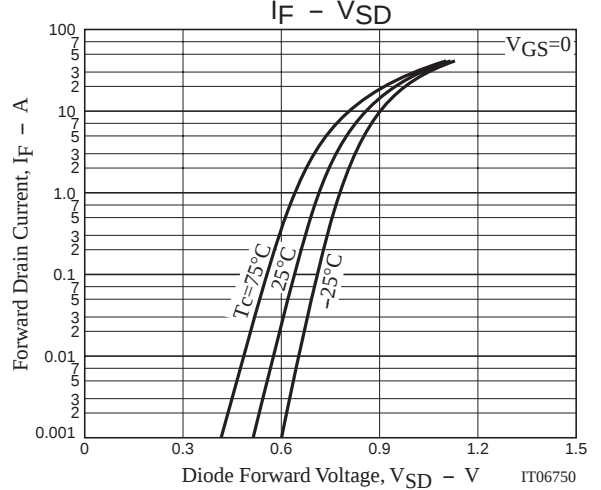
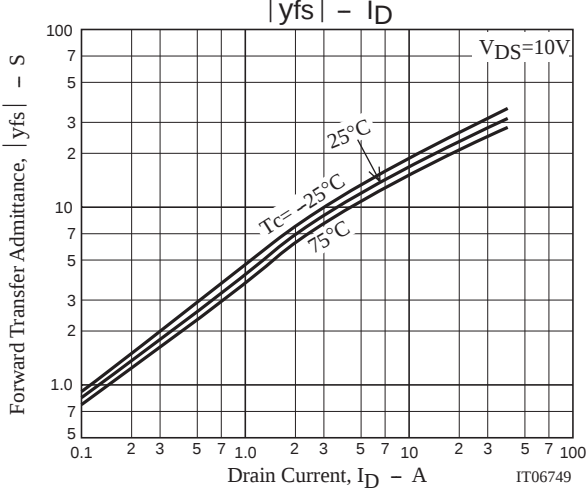
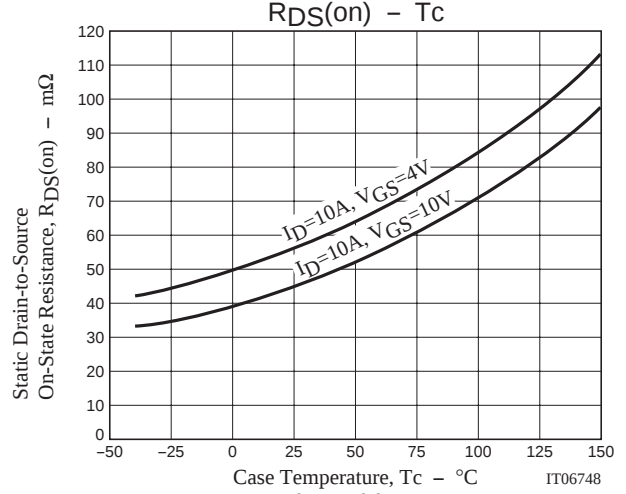
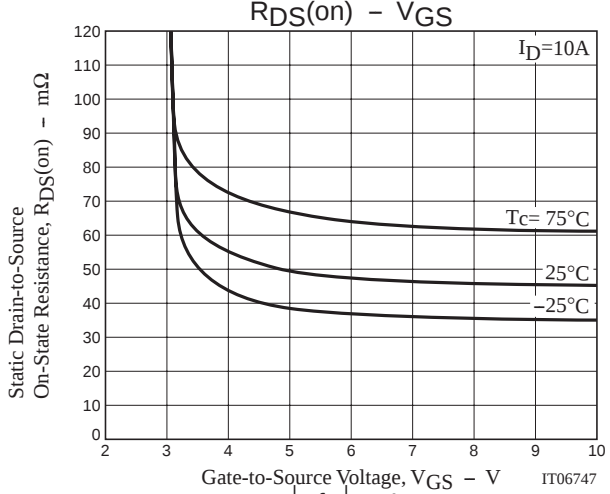
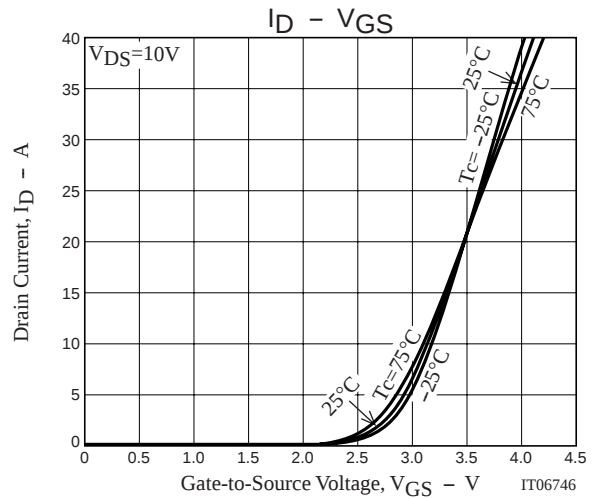
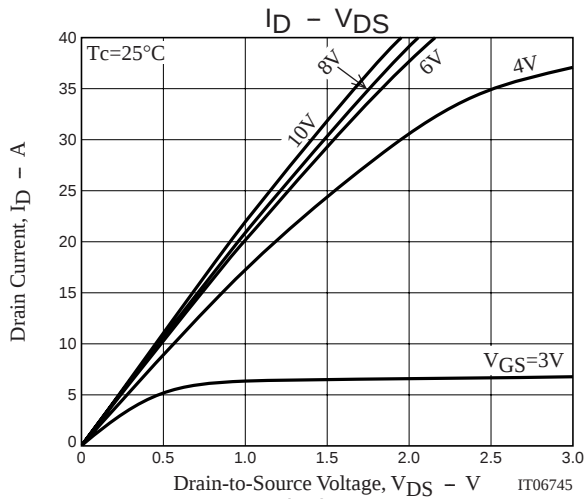


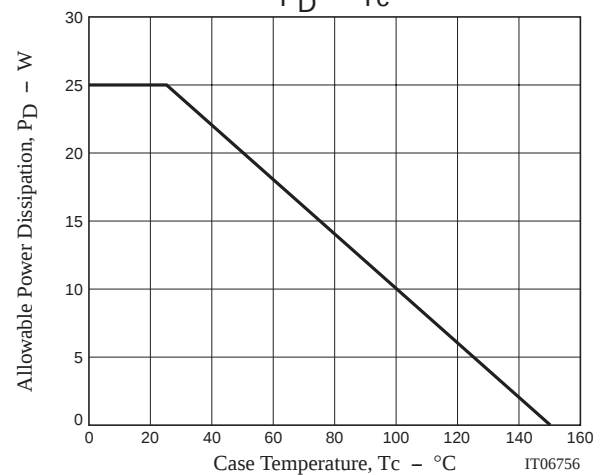
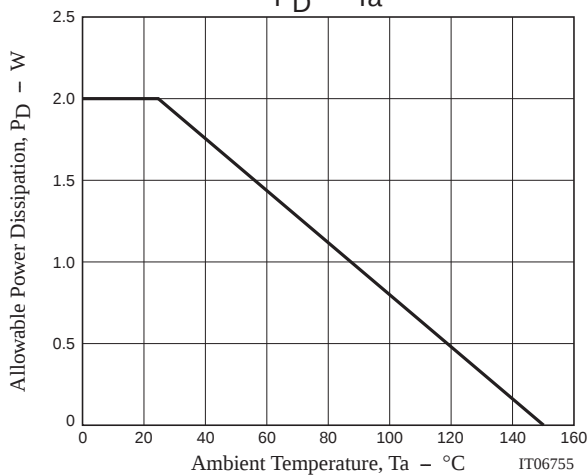
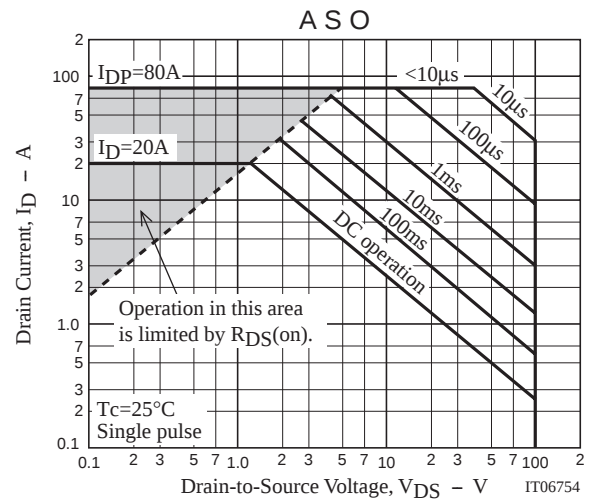
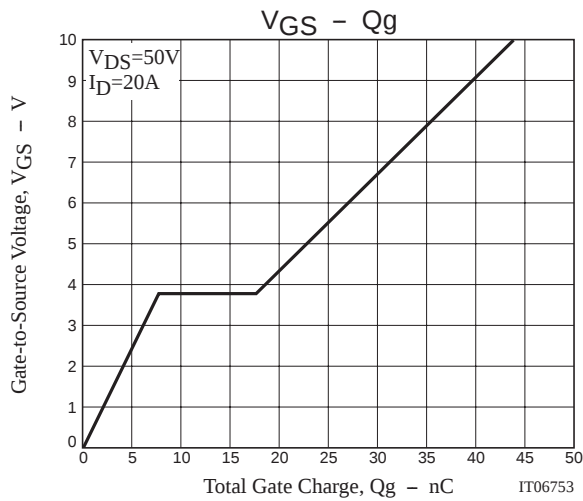
Switching Time Test Circuit



Unclamped Inductive Test Circuit







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